

LIGITEK

NPN SILICOM PHOTOTRANSISTOR LED LAMPS		LPT2023		SERIES		
<p align="center"><i>Package Dimension</i></p>				<p align="center"><i>Features</i></p> <ul style="list-style-type: none"> • High illumination sensitivity • Stable characteristics • Spectrally and mechanically matched with IR emitter 		
				<p align="center"><i>Description</i></p> <p>The LPT2023 series are silicon nitride passivated NPN planar phototransistors with exceptionally stable characteristics and high illumination sensitivity the cases of LPT2023 are encapsulated in clear plastic T1 package individually</p>		
<p>MAXIMUM RATINGS (TA=25°C)</p>						
PARAMETER		MAXIMUM RATINGS		UNIT		
Power Dissipation		100		mw		
Collect-Emmitter Voltage		30		V		
Emmitter-Collect Voltage		5		V		
Operating Temperature		-50°C TO +100°C				
Storage Temperature Range		-50°C TO +100°C				
Lead Soldering Temperature (1.6mm From Body)		260°C for 5 seconds				
<p>ELECTRICAL CHARACTERISTICS (TA=25°C)</p>						
PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	TEST CONDITION
Collect-Emmitter Breakdown Voltage	V(BR)CEO	30			v	Ic=1mA Ee=0mw/cm ²
Emmitter-Collector Breakdown Voltage	V(BR)ECO	5			v	Ie=100mA Ee=0mw/cm ²
Collect-Emmitter Saturation Voltage	VCE(sat)			0.4	v	Ic=0.5mA Ee=20mw/cm ²
Rise Time	tr		5		μs	Vce=30v Ic=800μA, RL=1KΩ
Fall Time	tf		5		μs	
Collector Dark Current	Iceo			100	nA	Vce=10v Ee=0mw/cm ²
On State Collector Current	Ip(on)	1		2	mA	Vce=5v Ee=1mW/cm ² λ=940nm
		2		4	mA	
		4		8	mA	
		8			mA	
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